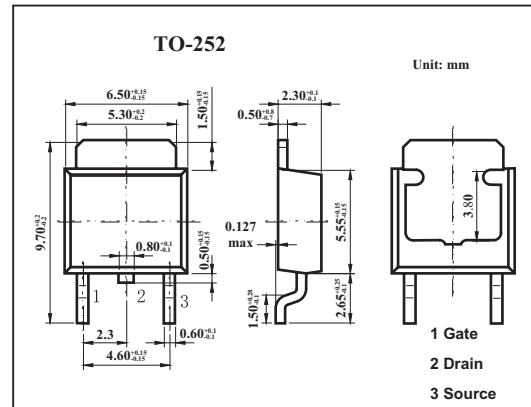
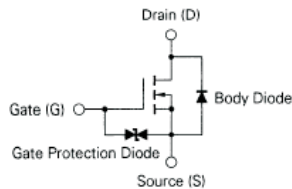


■ Features

- Low on-resistance  
R<sub>DS(on)</sub>=0.65 Ω (V<sub>GS</sub>=10V, I<sub>D</sub>=2A)
- Low C<sub>iss</sub> C<sub>iss</sub>=300pF typ
- Built-in G-S Gate Protection Diode
- High Avalanche Capability Ratings



■ Absolute Maximum Ratings Ta = 25°C

Parameter	Symbol	Rating	Unit
Drain to source voltage	V <sub>DSS</sub>	180	V
Gate to source voltage	V <sub>GSS</sub>	±20	V
Drain current	I <sub>D</sub>	±4.0	A
Power dissipation	P <sub>D</sub>	20	W
Channel temperature	T <sub>ch</sub>	150	°C
Storage temperature	T <sub>stg</sub>	-55 to +150	°C

■ Electrical Characteristics Ta = 25°C

Parameter	Symbol	Testconditons	Min	Typ	Max	Unit
Drain cut-off current	I <sub>DSS</sub>	V <sub>DS</sub> =180V, V <sub>GS</sub> =0			100	μ A
Gate leakage current	I <sub>GSS</sub>	V <sub>GS</sub> =±20V, V <sub>DS</sub> =0			±10	μ A
Gate to Source Cutoff Voltage	V <sub>GS(off)</sub>	V <sub>DS</sub> =10V, I <sub>D</sub> =1mA	2.0		4.0	V
Forward transfer admittance	Y <sub>fs</sub>	V <sub>DS</sub> =10V, I <sub>D</sub> =2.0A	0.5			S
Drain to source on-state resistance	R <sub>DS(on)</sub>	V <sub>GS</sub> =10V, I <sub>D</sub> =2.0A		0.52	0.65	Ω
Input capacitance	C <sub>iss</sub>	V <sub>DS</sub> =10V, V <sub>GS</sub> =0, f=1MHZ		300		pF
Output capacitance	C <sub>oss</sub>			170		pF
Reverse transfer capacitance	C <sub>rss</sub>			50		pF
Turn-on delay time	t <sub>d(on)</sub>	I <sub>D</sub> =2A, V <sub>GS(on)</sub> =10V, R <sub>L</sub> =50 Ω		9		ns
Rise time	t <sub>r</sub>			12		ns
Turn-off delay time	t <sub>d(off)</sub>			28		ns
Fall time	t <sub>f</sub>			12		ns